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PMV32UP

20 V, 4 A P-channel Trench MOSFET Rev. 1 — 11 March 2011

Product data sheet

Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 1.8 V drain-source on-state resistance rated
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-8	-	8	V
I_D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}$	[1]	-	-	-4	Α
Static char	acteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A};$ $T_j = 25 ^{\circ}\text{C}$		-	32	36	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



20 V, 4 A P-channel Trench MOSFET

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source	<u> 3</u>	D
3	D	drain	1 2	G T
			SOT23 (TO-236AB)	S 017aaa094

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMV32UP	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMV32UP	NF%

[1] % = placeholder for manufacturing site code

20 V, 4 A P-channel Trench MOSFET

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-20	٧
V_{GS}	gate-source voltage			-8	8	V
I_D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}$	<u>[1]</u>	-	-4	Α
		$V_{GS} = -4.5 \text{ V}; T_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u>	-	-2.5	Α
I _{DM}	peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \text{ µs}$		-	-16	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	510	mW
			[1]	-	930	mW
		T _{sp} = 25 °C		-	4150	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-1	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

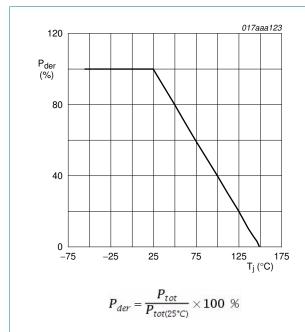


Fig 1. Normalized total power dissipation as a function of junction temperature

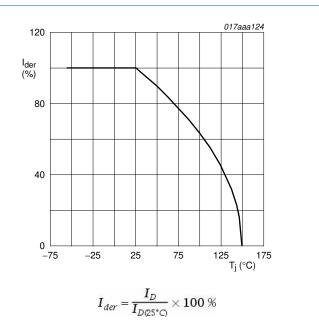
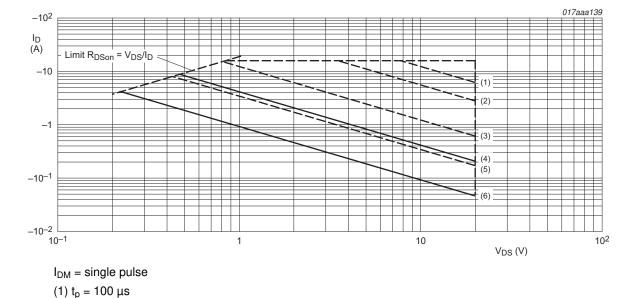


Fig 2. Normalized continuous drain current as a function of junction temperature

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20 V, 4 A P-channel Trench MOSFET



- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) DC; $T_{sp} = 25$ °C
- $(5) t_p = 100 \text{ ms}$
- (6) DC; T_{amb} = 25 °C; drain mounting pad 6 cm²

Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source Fig 3.

6. Thermal characteristics

Table 6. **Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air	<u>[1]</u>	-	207	245	K/W
	from junction to ambient		[2]	-	117	135	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	25	30	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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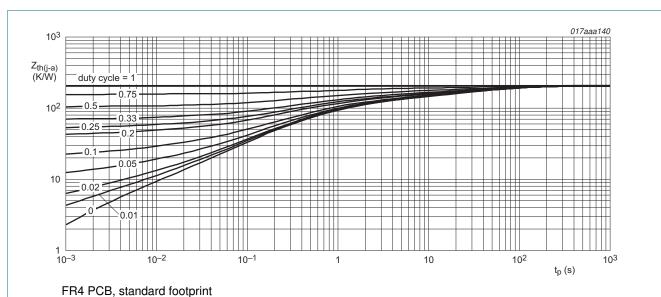


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

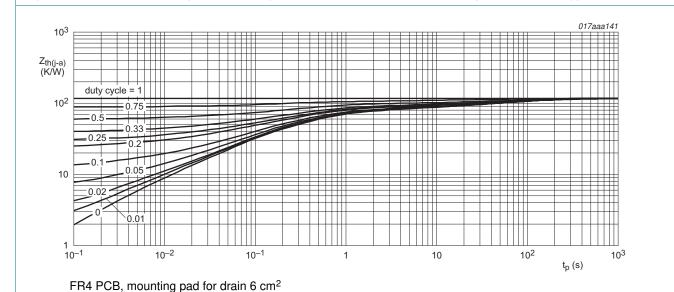


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, 4 A P-channel Trench MOSFET

7. Characteristics

Table 7. Characteristics

Table 1.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_{D} = -2.4 A; T_{j} = 25 °C	-	32	36	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	46	53	mΩ
		V_{GS} = -2.5 V; I_D = -2.0 A; T_j = 25 °C	-	40	46	mΩ
		$V_{GS} = -1.8 \text{ V}; I_D = -1.8 \text{ A}; T_j = 25 \text{ °C}$	-	55	73	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$	-	13	-	S
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = -1 A$; $V_{DS} = -10 V$; $V_{GS} = -4.5 V$;	-	15.5	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	2.7	-	nC
Q_{GD}	gate-drain charge		-	2.2	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = -10 \text{ V}; f = 1 \text{ MHz};$	-	1890	-	рF
Coss	output capacitance	T _j = 25 °C	-	175	-	рF
C _{rss}	reverse transfer capacitance		-	112	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; V_{GS} = -5 V; $R_{G(ext)}$ = 6 Ω ;	-	13	-	ns
t _r	rise time	$T_j = 25 ^{\circ}C; I_D = -1 A$	-	21	-	ns
t _{d(off)}	turn-off delay time		-	95	-	ns
t _f	fall time		-	33	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = -2.4 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_i = 25 \text{ °C}$	-	-0.75	-1	V

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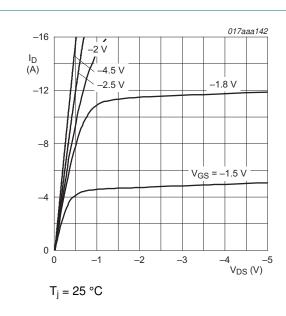
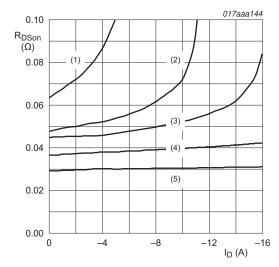


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$

(1) $V_{GS} = -1.5 \text{ V}$

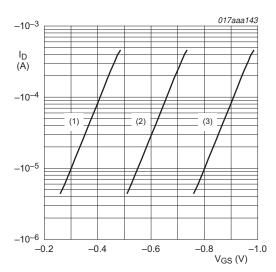
(2) $V_{GS} = -1.8 \text{ V}$

(3) $V_{GS} = -2.0 \text{ V}$

 $(4) V_{GS} = -2.5 V$

(5) $V_{GS} = -4.5 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



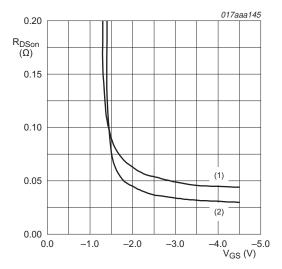
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = -3 \, V$

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



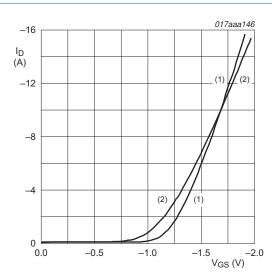
 $I_D = -2.4 A$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_j = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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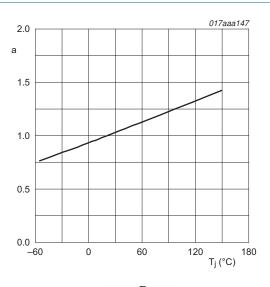


 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_i = 25 \, ^{\circ}C$$

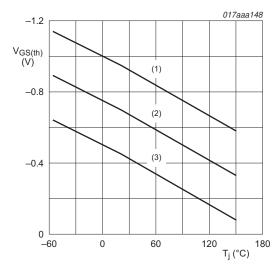
(2) $T_i = 150 \, ^{\circ}\text{C}$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

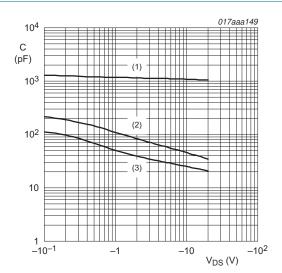
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 I_D = -0.25 mA; V_{DS} = V_{GS}

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature

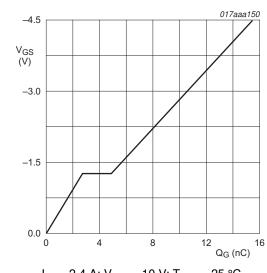


 $f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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 I_D = -2.4 A; V_{DS} = -10 V; T_{amb} = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

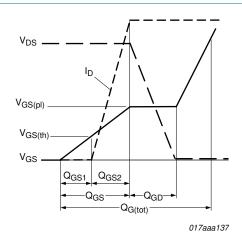
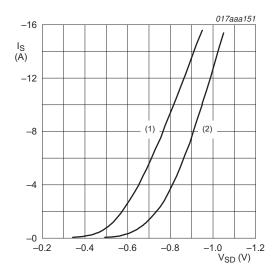


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

(1) $T_j = 150 \, ^{\circ}C$

(2) $T_j = 25 \, {}^{\circ}\text{C}$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Package outline

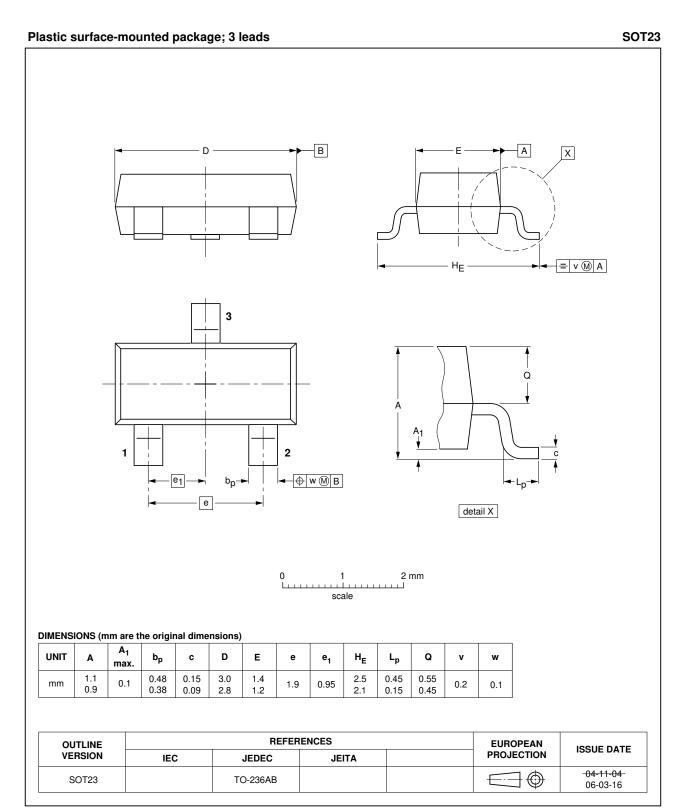
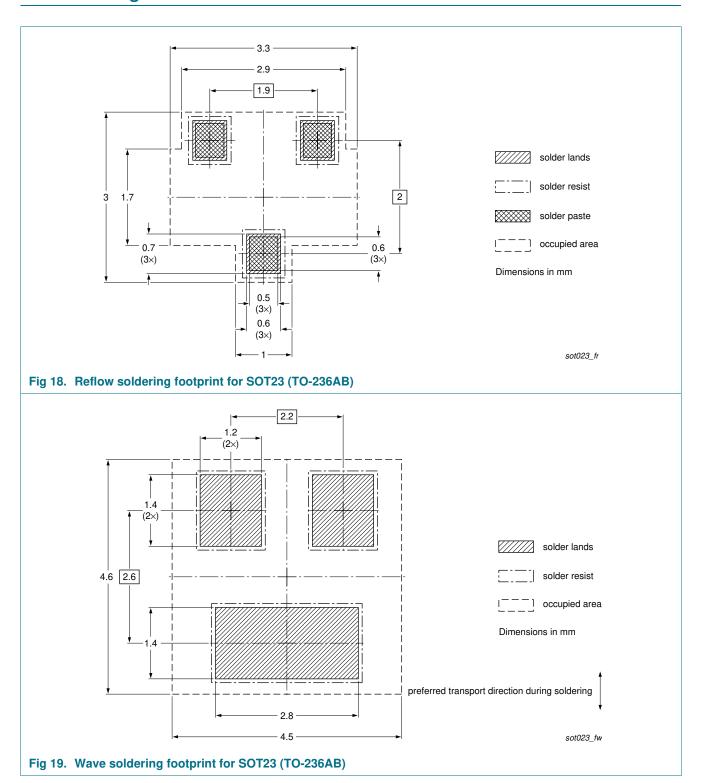


Fig 17. Package outline SOT23 (TO-236AB)

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9. Soldering



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10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMV32UP v.1	20110311	Product data sheet	-	-

20 V, 4 A P-channel Trench MOSFET

11. Legal information

11.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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